100V N-Ch Power MOSFET

DS(on),typ			Ω
DS(on),typ			Ω

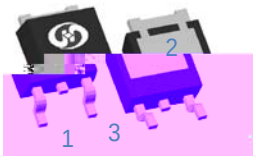
Feature

- High Speed Power Switching, Logic Level
- Enhanced Body diode dv/dt capability
- Enhanced Avalanche Ruggedness
- 100% UIS Tested, 100% Rg Tested
- Lead Free, Halogen Free

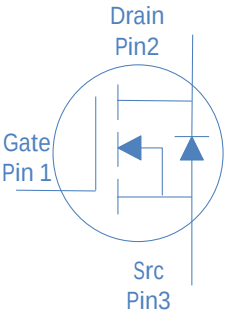
Application

- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit
- DC/DC in Telecoms and Inductrial

TO-252



TO-251



	TO-251	
	TO-252	

=25 (unless otherwise specified)

		=25		
		=100		
Avalanche Energy, Single Pulse	E	=25		
Power Dissipation		=25		W
Operating and Storage Temperature				

Thermal Resistance Junction-Ambient	θ		/W
Thermal Resistance Junction-Case	θ		/W

Fig 1. Typical Output Characteristics

Figure 2. On-Resistance vs. Gate-Source Voltage

Figure 3. On-Resistance vs. Drain Current and Gate Voltage

Figure 4. Normalized On-Resistance vs. Junction Temperature

Figure 5. Typical Transfer Characteristics

Figure 6. Typical Source-Drain Diode Forward Voltage

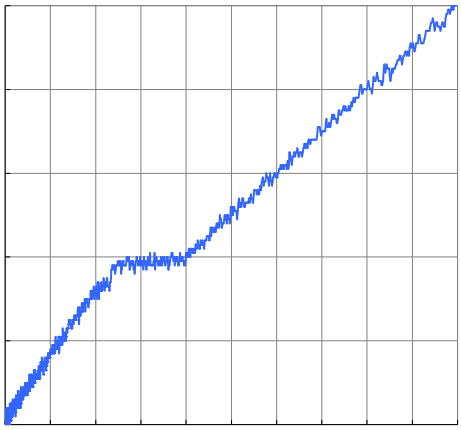
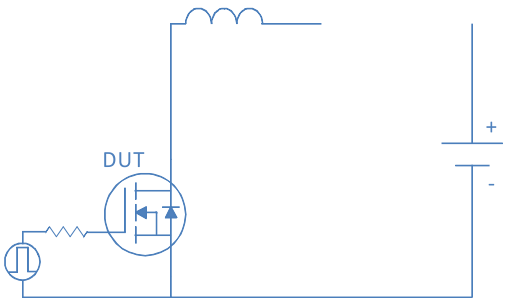
Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage	Figure 8. Typical Capacitance vs. Drain-to-Source Voltage
	

Figure 9. Maximum Safe Operating Area	Figure 10. Maximun Drain Current vs. Case Temperature
I_D (A) DC =25 ° C V	

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case

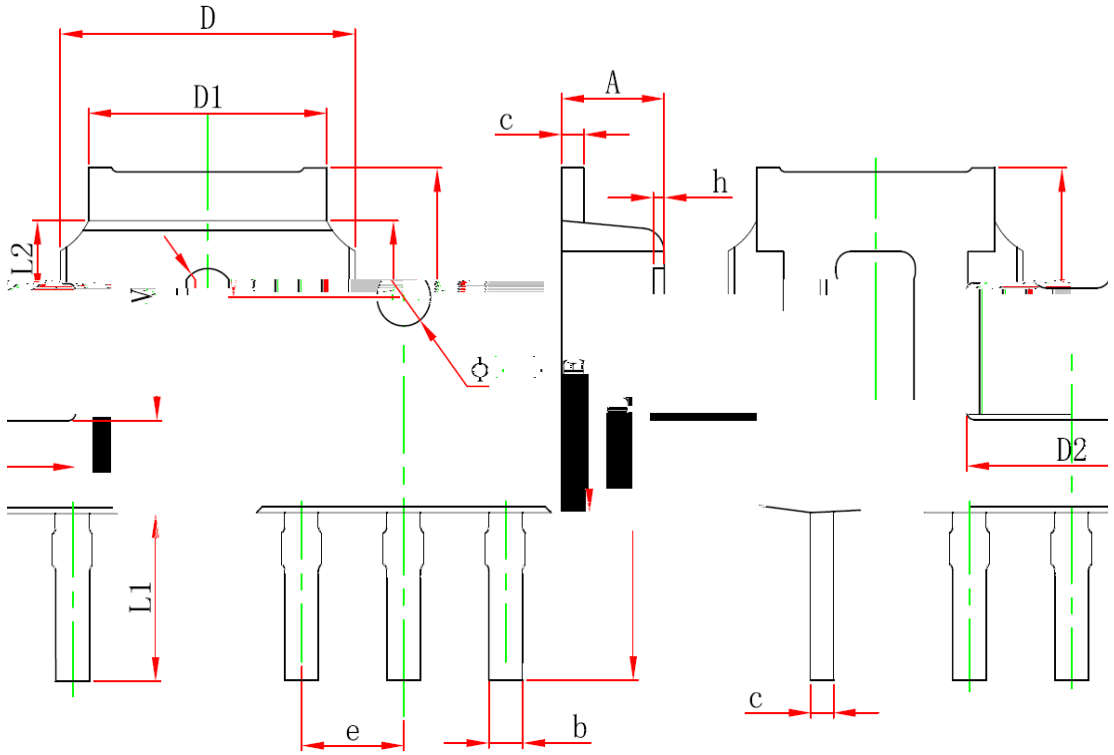
Inductive switching Test	

Gate Charge Test	

Uclamped Inductive Switching (UIS) Test	
	

Package Outline

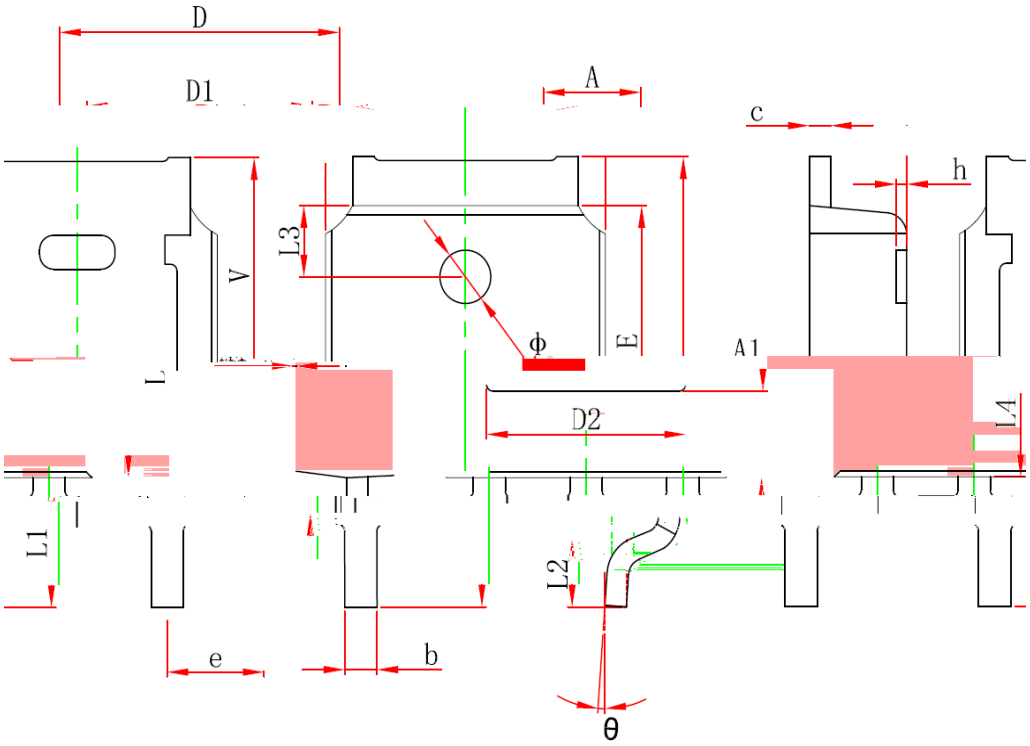
TO-251, 3 leads



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
b	0.660	0.860	0.026	0.034

Package Outline

TO-252, 2 leads



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
094	A	2.200	2.400	0.087	0.(
005	A1	0.000	0.127	0.000	0.(
034	b	0.660	0.860	0.026	0.(
023	c	0.460	0.580	0.018	0.(
0.264	D	6.500	6.700	0.256	

[redacted]